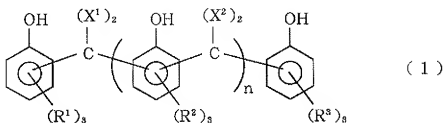


IN THE CLAIMS:

The claims have not been amended, and are set forth here in full for the Examiner's convenience.

1. (Original) A field effect transistor comprising at least a substrate, an organic semiconductor layer, an insulating layer, and a conductive layer, wherein the insulating layer comprises a cured product of a phenol resin represented by a following general formula (1):



(wherein, R¹, R² and R³ are each independently at least one selected from the group consisting of hydrogen atom, halogen atom, hydroxymethyl group, alkyl group having 1 to 12 carbon atoms, alkenyl group, alkynyl group, alkoxy group, alkylthio group, and alkyl ester group, X¹ and X² are each independently at least one selected from the group consisting of hydrogen atom, alkyl group having 1 to 12 carbon atoms, alkenyl group, alkynyl group, and aryl group, and n is an integer of 0 to 2,000.)

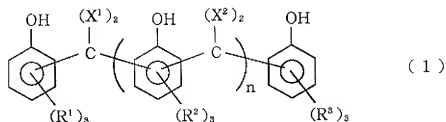
2. (Original) The field effect transistor according to claim 1, wherein the conductive layer comprises a gate electrode, a source electrode, and a drain electrode, the insulating layer includes a gate insulating layer, and the gate insulating layer is a cured product of a phenol resin represented by the above general formula (1).

3. (Original) The field effect transistor according to claim 2, wherein the thickness of the gate insulating layer is 100 nm to 1 μ m.

4. (Original) The field effect transistor according to any one of claims 1 to 3, wherein part or all of the conductive layer comprises an agglomerate of conductive fine particles having a primary particle diameter of 5 nm to 2 μ m.

5. (Original) A process for producing a field effect transistor comprising a substrate, an organic semiconductor layer, an insulating layer, and a conductive layer, the process comprising the steps of:

coating a thermosetting resin composition containing at least a phenol resin represented by the following general formula (1):



(wherein, R¹, R² and R³ are each independently at least one selected from the group consisting of hydrogen atom, halogen atom, hydroxymethyl group, alkyl group having 1 to 12 carbon atoms, alkenyl group, alkynyl group, alkoxy group, alkylthio group, and alkyl ester group, X¹ and X² are each independently at least one selected from the group consisting of hydrogen atom, alkyl group having 1 to 12 carbon atoms, alkenyl group, alkynyl group, and aryl group, and n is an integer of 0 to 2,000.) and

heating it to form the insulating layer.

6. (Original) The process for producing a field effect transistor according to claim 5, wherein part or all of the conductive layer is formed by applying a solution, dispersion, or paste of a conductive material or a precursor of the conductive material and heating it.

7. (Original) The process for producing a field effect transistor according to claim 5, wherein the softening point of the phenol resin contained in the thermosetting resin composition is in the range of 70 to 130°C.